

Chapter 2

2-2) The specific density of tungsten is 18.8 g/cm^3 , and its atomic weight is 184.0. Assume that there are two free electrons per atom. Calculate the concentration of free electrons.

Answer

$$d = 18.8 \text{ g/cm}^3 = 18.8 * 10^3 \text{ kg/m}^3$$

$$A = 184.0$$

$$\nu = 2$$

$$n = \frac{A_0 d \nu * 10^3}{A} = \frac{6.023 * 10^{23} * 18.8 * 10^3 * 2 * 10^3}{184.0} = 1.23 * 10^{29} \text{ electron/m}^3$$

2-3)

(a) Compute the conductivity of copper for which $\mu = 34.8 \text{ cm}^2/\text{Vs}$ and $d = 8.9 \text{ g/cm}^3$.

(b) If an electrical field is applied across such a copper bar with an intensity 10 V/cm , find the average velocity of the free electrons.

Answer

(a)

$$\mu = 34.8 \text{ cm}^2/\text{Vs} = 34.8 * 10^{-4} \text{ m}^2/\text{Vs}$$

$$d = 8.9 \text{ g/cm}^3 = 8.9 * 10^3 \text{ kg/m}^3$$

$$\nu = 1 \text{ electron/atom}$$

$$A = 63.54$$

$$n = \frac{A_0 d \nu * 10^3}{A} = \frac{6.023 * 10^{23} * 8.9 * 10^3 * 1 * 10^3}{63.54} = 8.4 * 10^{28} \text{ electron/m}^3$$

$$\sigma = nq\mu = 8.4 * 10^{28} * 1.6 * 10^{-19} * 34.8 * 10^{-4} = 4.697 * 10^7 (\Omega \text{ m})^{-1}$$

(b)

$$E = 10 \text{ V/cm} = 10^3 \text{ V/m}$$

$$v = \mu E = 10^3 * 34.8 * 10^{-4} = 3.48 \text{ m/s}$$

2-4) Compute the mobility of free electrons in aluminum for which the density is 2.70 g/cm^3 and the resistivity is $3.44 * 10^{-6} \Omega \text{ cm}$. Assume that aluminum has three valance electrons /atom.

Answer

$$d = 2.7 \text{ g/cm}^3 = 2.7 * 10^3 \text{ kg/m}^3$$

$$\rho = 3.44 * 10^{-6} \Omega \text{ cm} = 3.44 * 10^{-8} \Omega \text{ m}$$

$$\sigma = \frac{1}{\rho} = 2.9 * 10^7 (\Omega \text{ m})^{-1}$$

$$A = 26.98$$

$$n = \frac{A_0 d \nu * 10^3}{A} = \frac{6.023 * 10^{23} * 2.7 * 10^3 * 3 * 10^3}{26.98} = 1.8 * 10^{29} \text{ electron/m}^3$$

$$\rho = nq\mu$$

$$\mu = \frac{\sigma}{nq} = \frac{2.9 * 10^7}{1.8 * 10^{29} * 1.6 * 10^{-19}} = .001 m^2 / Vs$$

2-5) The resistance of No. 18 copper wire (diameter = 1.03 mm) is 6.51Ω per 1000ft. The concentration of free electrons in copper is $8.4 * 10^{28}$ electrons / m^3 . If the current is 2 A, find the (a) drift velocity (b) mobility (c) conductivity

Answer

$$d = 1.03 mm$$

$$r = .565 * 10^{-3} m$$

$$A = \pi r^2 = \frac{\pi d^2}{4} = 8.66 * 10^{-7} m^2$$

$$R = 6.51 \Omega$$

$$L = 1000 ft = 1000 * .305 = 305 m$$

$$n = 8.4 * 10^{28} \text{ electrons} / m^3$$

$$I = 2 A$$

$$\sigma = \frac{L}{RA} = \frac{305}{6.51 * 8.66 * 10^{-7}} = 5.41 * 10^7 (\Omega m)^{-1}$$

$$\mu = \frac{\sigma}{nq} = \frac{5.41 * 10^7}{8.4 * 10^{28} * 1.6 * 10^{-19}} = .004 m^2 / Vs$$

$$v = \mu E = \mu \frac{V}{L} = \mu \frac{IR}{L} = .004 * \frac{2 * 6.51}{305} = 1.72 * 10^{-4} m / s$$

2-7)

(a) Find the concentration of holes and of electrons in a p-type germanium at 300K if the conductivity is $100 (\Omega m)^{-1}$

(b) Repeat part a for n-type silicon if the conductivity is $0.1 (\Omega m)^{-1}$

Answer

a)

$$n_i = 2.5 * 10^{13} \text{ electrons} / cm^3$$

$$\mu_p = 1800 cm^2 / Vs$$

$$\sigma = pq\mu_p$$

$$p = \frac{\sigma}{q\mu_p} = \frac{100}{1.6 * 10^{-19} * 1800} = 3.47 * 10^{17} \text{ holes} / cm^3$$

$$n = \frac{n_i^2}{P} = \frac{(2.5 * 10^{13})^2}{3.47 * 10^{17}} = 1.8 * 10^9 \text{ electrons} / cm^3$$

b)

$$n_i = 1.5 * 10^{10} \text{ electrons / cm}^3$$

$$\mu_n = 1300 \text{ cm}^2 / \text{Vs}$$

$$\sigma = nq\mu_n$$

$$n = \frac{\sigma}{q\mu_n} = \frac{0.1}{1.6 * 10^{-19} * 1300} = 4.8 * 10^{14} \text{ electrons / cm}^3$$

$$p = \frac{n_i^2}{n} = \frac{(1.5 * 10^{10})^2}{4.8 * 10^{14}} = 4.68 * 10^5 \text{ holes / cm}^3$$

2-8)

a) Show that the resistivity of intrinsic germanium at 300K is $45 \Omega m$.

b) If a donor-type impurity is added to the extent of 1 atom per 10^8 germanium atoms prove that the resistivity drops to $3.7 \Omega cm$

Answer

a)

$$n_i = 2.5 * 10^{13} \text{ electrons / cm}^3$$

$$\mu_p = 1800 \text{ cm}^2 / \text{Vs}$$

$$\mu_n = 3800 \text{ cm}^2 / \text{Vs}$$

$$\begin{aligned} \sigma &= n_i q (\mu_p + \mu_n) = 2.5 * 10^{13} * 1.6 * 10^{-19} * (1800 + 3800) \\ &= 0.0224 (\Omega cm)^{-1} \end{aligned}$$

$$\rho = \frac{1}{\sigma} = 44.64 \Omega cm \cong 45 \Omega cm$$

b)

n-type

$$d = 5.32 \text{ g / cm}^3$$

$$A = 72.6$$

$$N = \frac{A_0 d}{A} = \frac{6.023 * 10^{23} * 5.32}{72.6} = 4.41 * 10^{22} \text{ atom / cm}^3$$

$$n \cong N_D = \frac{4.41 * 10^{22}}{10^8} = 4.41 * 10^{14} \quad , \text{ as for each } 10^8 \text{ Ge atom there are one donor atom}$$

$$\sigma = nq\mu_n = 4.41 * 10^{14} * 1.6 * 10^{-19} * 3800 = 0.268 (\Omega m)^{-1}$$

$$\rho = \frac{1}{\sigma} = 3.72 \Omega m$$

2-9)

a) Find the resistivity of intrinsic silicon at 300K.

b) If a donor-type impurity is added to the extent of 1 atom per 10^8 silicon atoms, find the resistivity.

Answer

a)

$$n_i = 1.5 * 10^{10} \text{ electrons / cm}^3$$

$$\mu_p = 500 \text{ cm}^2 / \text{Vs}$$

$$\mu_n = 1300 \text{ cm}^2 / \text{Vs}$$

$$\sigma = n_i q (\mu_p + \mu_n) = 1.5 * 10^{10} * 1.6 * 10^{-19} * (1300 + 500)$$

$$= 4.32 * 10^{-6} (\Omega \text{ cm})^{-1}$$

$$\rho = \frac{1}{\sigma} = 2.3 * 10^5 \Omega \text{ cm}$$

b)

n-type

$$d = 2.33 \text{ g / cm}^3$$

$$A = 28.1$$

$$N = \frac{A_0 d}{A} = \frac{6.023 * 10^{23} * 2.33}{28.1} = 4.99 * 10^{22} \text{ atom / cm}^3$$

$$n \cong N_D = \frac{4.99 * 10^{22}}{10^8} = 4.99 * 10^{14} \quad , \text{ as for each } 10^8 \text{ Ge atom there are one donor atom}$$

$$\sigma = nq \mu_n = 4.99 * 10^{14} * 1.6 * 10^{-19} * 1300 = 0.104 (\Omega \text{ m})^{-1}$$

$$\rho = \frac{1}{\sigma} = 9.634 \Omega \text{ m}$$

2-10) Consider intrinsic germanium at room temperature (300K). By what percentage does the conductivity increase per degree rise in temperature?

Answer

$$\sigma_{301} = \sigma_0 e^{-\frac{E_g}{2kT_{301}}}$$

$$\sigma_{300} = \sigma_0 e^{-\frac{E_g}{kT_{300}}}$$

$$\frac{\sigma_{301}}{\sigma_{300}} = \frac{\sigma_0 e^{-\frac{E_g}{2kT_{301}}}}{\sigma_0 e^{-\frac{E_g}{kT_{300}}}} = e^{-\frac{E_g}{2kT_{301}} + \frac{E_g}{kT_{300}}} = e^{-\frac{E_g}{2k} \left(\frac{1}{301} - \frac{1}{300} \right)}$$

$$= e^{-\frac{.67}{2 * 8.62 * 10^{-5}} \left(\frac{1}{301} - \frac{1}{300} \right)} = 1.044$$

Where $E_g = .67 \text{ eV}$, $k = 8.62 * 10^{-5} \text{ eV / K}$

$$\sigma_{301} = 1.044 * \sigma_{300}$$

$$\text{conductivity increase} = \frac{\sigma_{301} - \sigma_{300}}{\sigma_{300}} = \frac{1.044 * \sigma_{300} - \sigma_{300}}{\sigma_{300}} * 100 = 4.4\%$$

2-11) Repeat Prob. 2-10 for intrinsic silicon.

Answer

$$\sigma_{301} = \sigma_0 e^{-\frac{E_g}{2kT_{301}}}$$

$$\sigma_{300} = \sigma_0 e^{-\frac{E_g}{kT_{300}}}$$

$$\frac{\sigma_{301}}{\sigma_{300}} = \frac{\sigma_0 e^{-\frac{E_g}{2kT_{301}}}}{\sigma_0 e^{-\frac{E_g}{2kT_{300}}}} = e^{-\frac{E_g}{2kT_{301}} + \frac{E_g}{2kT_{300}}} = e^{-\frac{E_g}{2k} \left(\frac{1}{301} - \frac{1}{300} \right)}$$

$$= e^{-\frac{1.1}{2 * 8.62 * 10^{-5}} \left(\frac{1}{301} - \frac{1}{300} \right)} = 1.073$$

Where $E_g = 1.1 eV$, $k = 8.62 * 10^{-5} eV / K$

$$\sigma_{301} = 1.073 * \sigma_{300}$$

$$\text{conductivity increase} = \frac{\sigma_{301} - \sigma_{300}}{\sigma_{300}} = \frac{1.073 * \sigma_{300} - \sigma_{300}}{\sigma_{300}} * 100 = 7.3\%$$